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#### 40V 175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>C</sub> = +25°C
40V	$15m\Omega @ V_{GS} = 10V$	42A

## **Description and Applications**

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

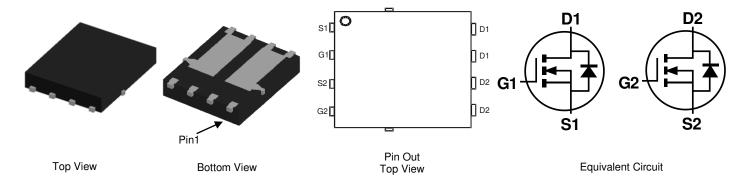
- Backlighting
- Power Management Functions
- DC-DC Converters

#### **Features and Benefits**

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

#### **Mechanical Data**

- Case: PowerDI<sup>®</sup>5060-8 (Type C)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 63
- Weight: 0.097 grams (Approximate)



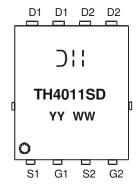
#### **Ordering Information** (Note 5)

-			
	Part Number	Case	Packaging
	DMTH4011SPDQ-13	PowerDI5060-8 (Type C)	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

# **Marking Information**



);; = Manufacturer's Marking
TH4011SD = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 18 = 2018)
WW = Week (01 to 53)



# **Maximum Ratings** (@ $T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DSS</sub>	40	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Continuous Drain Current (Note 7)	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	42 29.7	А
Continuous Drain Current (Note 6) $T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$		I <sub>D</sub>	11.1 7.8	А
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	60	Α	
Maximum Continuous Body Diode Forward Current (Note 7)	Is	3.3	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I <sub>SM</sub>	60	Α
Avalanche Current, L = 0.3mH		I <sub>AS</sub>	11.9	Α
Avalanche Energy, L = 0.3mH		Eas	21.4	mJ

### **Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 6) $T_A = +25^{\circ}C$		$P_{D}$	2.6	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>0JA</sub>	57	°C/W	
Total Power Dissipation (Note 7)	$P_{D}$	37.5	W	
Thermal Resistance, Junction to Case (Note 7)	R <sub>eJC</sub>	4	°C/W	
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to +175	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	40		_	V	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_		1	μΑ	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_		±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(TH)}$	2	1	4	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	11.6	15	mΩ	$V_{GS} = 10V, I_D = 20A$	
Diode Forward Voltage	$V_{SD}$	_	-	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	_	805	ı	рF	.,	
Output Capacitance	Coss	_	208	_	pF	$V_{DS} = 20V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Reverse Transfer Capacitance	Crss	_	15	_	pF		
Gate Resistance	$R_g$	_	2.76	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	$Q_g$	_	10.6	_	nC	V 00V I 00A	
Gate-Source Charge	$Q_{gs}$	_	2.2	_	nC	$V_{DS} = 20V, I_D = 20A,$ $V_{GS} = 10V$	
Gate-Drain Charge	$Q_{gd}$	_	2.7	_	nC		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	4.1	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	3.8	_	ns	$V_{DD} = 20V, V_{GS} = 10V,$ $R_G = 1.6\Omega, I_D = 20A$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	8.6	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	1.9	_	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	10.2	_	ns	I_ 15A di/dt 400A/vs	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	9.6	_	nC	I <sub>F</sub> = 15A, di/dt = 400A/μs	

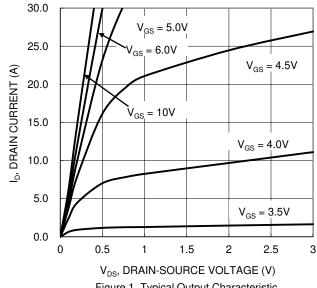
6. Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal bias to bottom layer 1inch square copper plate.

7. Thermal resistance from junction to soldering point (on the exposed drain pad).
8. Short duration pulse test used to minimize self-heating effect.

<sup>9.</sup> Guaranteed by design. Not subject to product testing.







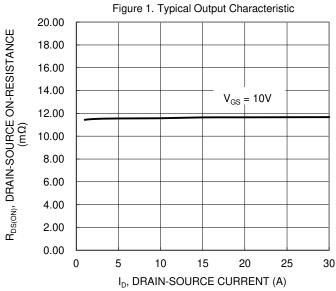


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

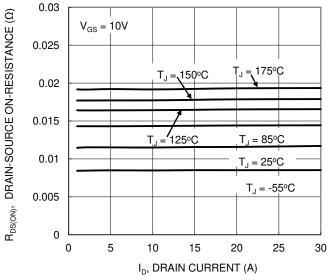
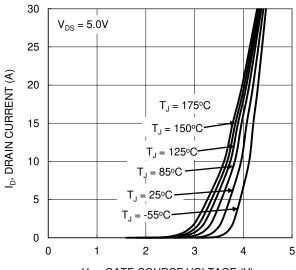


Figure 5. Typical On-Resistance vs. Drain Current and Temperature



V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

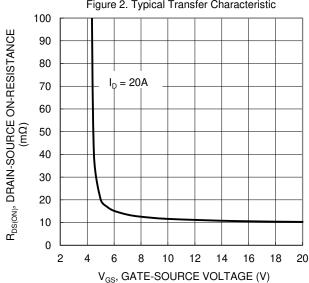


Figure 4. Typical Transfer Characteristic

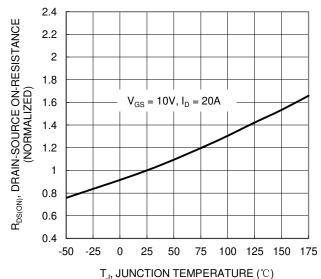


Figure 6. On-Resistance Variation with Temperature





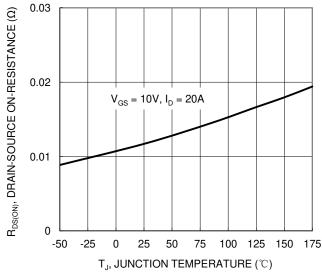


Figure 7. On-Resistance Variation with Temperature

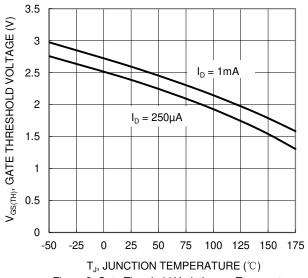
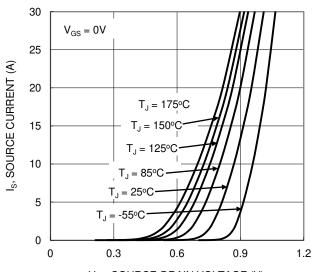


Figure 8. Gate Threshold Variation vs. Temperature



V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

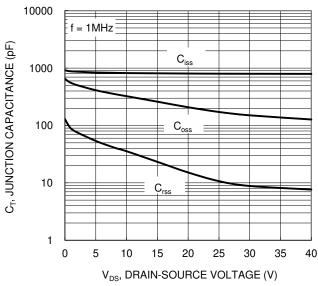
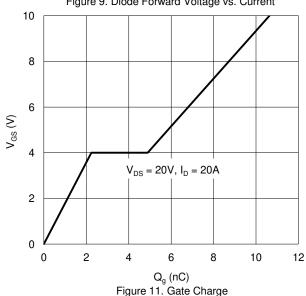


Figure 10. Typical Junction Capacitance



V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area

10

100

10

0.1

0.1

D, DRAIN CURRENT (A)

R<sub>DS(ON)</sub> Limited

> = 100ms P<sub>W</sub> = 10ms

 $T_{J(Max)} = 175^{\circ}C$   $T_{C} = 25^{\circ}C$ Single Pulse

DUT on Infinite Heatsink  $V_{GS} = 10V$ 

100



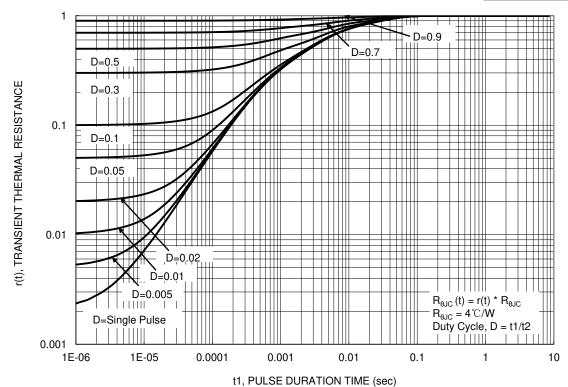


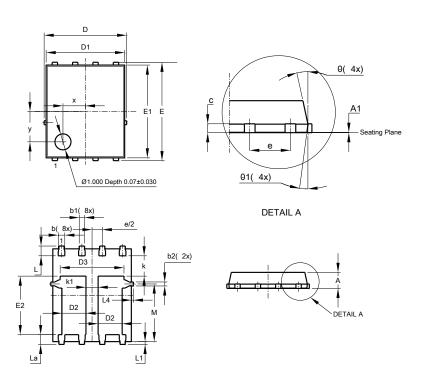
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8 (Type C)

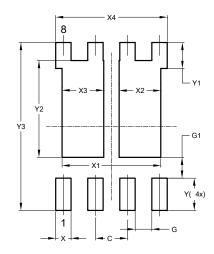


PowerDI5060-8 (Type C)					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0	0.05	0.02		
b	0.33	0.51	0.41		
b1	0.300	0.366	0.333		
b2	0.20	0.35	0.25		
С	0.23	0.33	0.277		
D	ļ	5.15 BSC	;		
D1	4.85	4.95	4.90		
D2	1.40 1.60 1.5				
D3	-	-	3.98		
Е	(	6.15 BSC	)		
E1	5.75	5.85	5.80		
E2	3.56 3.76 3		3.66		
е		1.27BSC	;		
k	-	-	1.27		
k1	0.56	-	-		
L	0.51	0.71	0.61		
La	0.51 0.71 0.		0.61		
L1	0.05	0.20 0.17			
L4	-	-	0.125		
М	3.50	3.71 3.60			
X	-	-	1.400		
у	-	-	1.900		
θ	10°	12°	11°		
θ1	6°	8°	7°		
All Dimensions in mm					

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8 (Type C)



Dimensions	Value			
	(in mm)			
C	1.270			
G	0.660			
G1	0.820			
Х	0.610			
X1	3.910			
X2	1.650			
Х3	1.650			
X4	4.420			
Υ	1.270			
Y1	1.020			
Y2	3.810			
Y3	6.610			



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